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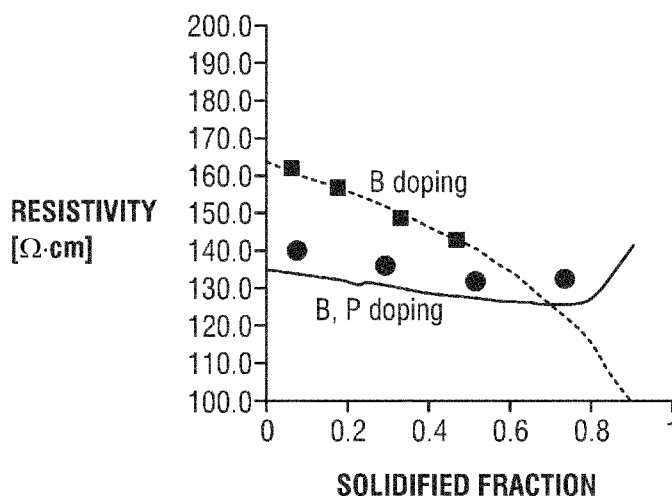
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(54) Title: METHOD OF MANUFACTURING SILICON SINGLE CRYSTAL, SILICON SINGLE CRYSTAL, AND WAFER

Fig. 3B

(57) **Abstract:** To provide a method of manufacturing silicon single crystal by manufacturing with a Czochralski method, p-type silicon single crystal from which a wafer having high resistivity, good radial uniformity of resistivity and less variation in resistivity can be obtained. P-type silicon single crystal 2 is grown with a Czochralski method from an initial silicon melt in which boron concentration is not higher than 4×10^{14} atoms/cm³ and a ratio of phosphorus concentration to boron concentration is not lower than 0.42 and not higher than 0.50.